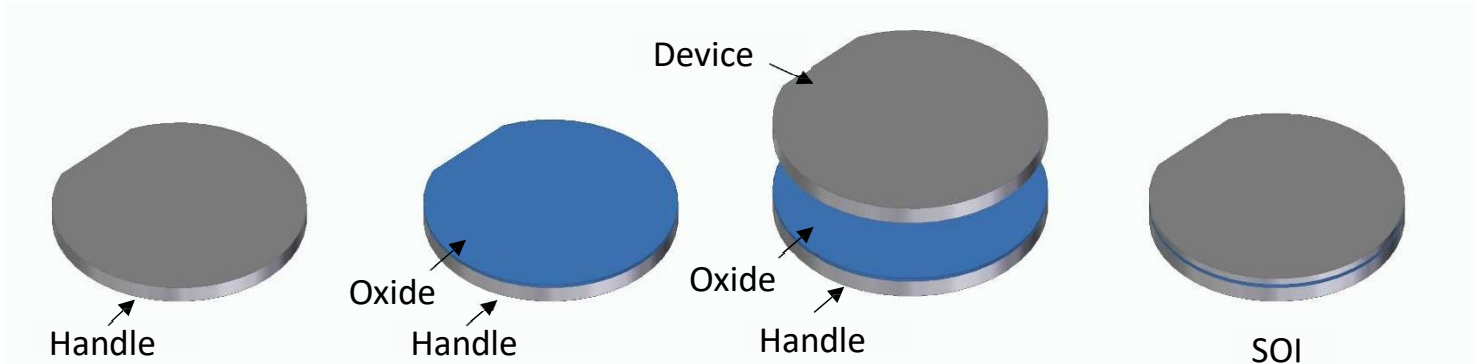
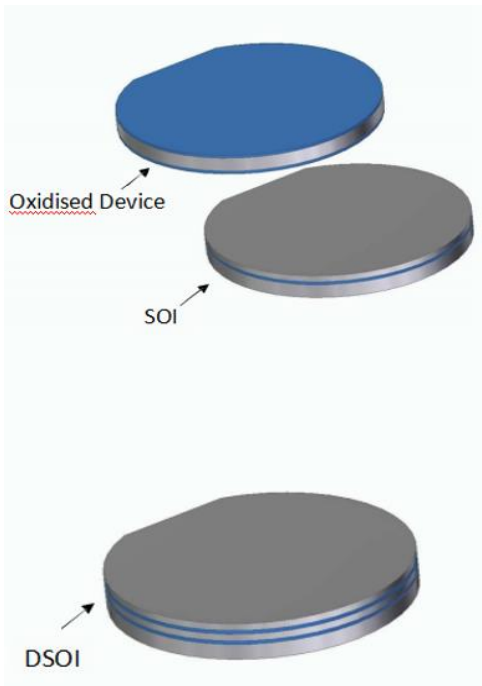


绝缘体上硅 SOI Solutions

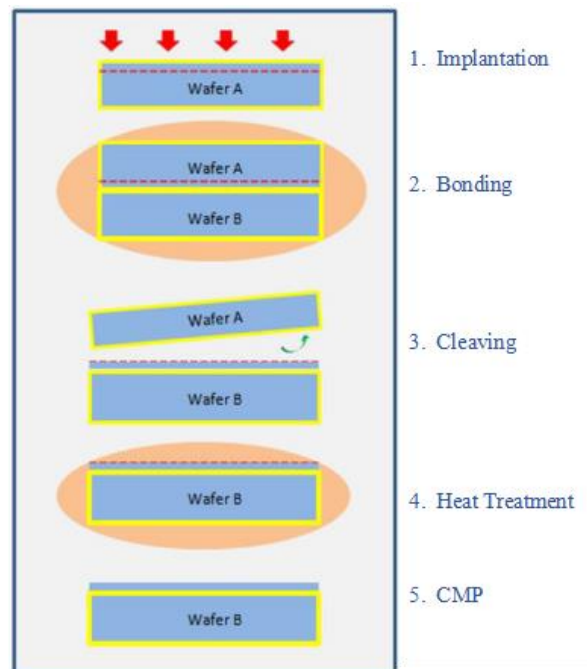


SOI (silicon on insulator, 绝缘体上硅) 被证明是高线性度、高效率、高集成无线系统半导体的首选解决方案。BonTek 可以提供世界领先的 4-8 英寸 SOI 晶片，我们对各种 SOI 基材均拥有丰富的经验，我们的应用工程团队在光学、惯性和其他 MEMS 领域都有丰富的经验，可以帮助客户选择最佳的参数组合，提供具有高性价比的定制化 SOI 解决方案。BonTek 会是您理想的 SOI 合作伙伴。

The SOI (Silicon on insulator) is proved to be the preferred solution for the high linearity, high efficiency and high integrated wireless system semiconductor. BonTek is a leading supplier of world class 100-200mm thick-film Silicon on Insulator wafers for a large range of IC and MEMS applications. With over 20 years' experience in SOI manufacturing, we offer an impressive specification range. Our highly skilled engineering team is experienced in optical, inertial, and other MEMS fields. They can support you to select the optimum combination of parameters for your requirements, ensuring that you receive the most cost-effective customised SOI solution for your application.



Double or Multi-Layer SOI 双层或多层 SOI



Thin-SOI 超薄 SOI 晶圆

我们还可根据需求，为您定制双层、多层或超薄绝缘体上硅 SOI 晶圆。具体规格请见下页。
Double, multi-layer or thin SOIs are available as required. Please find the specs in the next page.



加工能力 processing capacity

Parameter 参数	Specification Range 尺寸规格范围	
Wafer Diameter 直径	100, 125, 150 mm	200 mm
Handle Layer Specifications 衬底层规格		
Handle Thickness 衬底层厚度	200-1100 μm	450-1100 μm
Handle Thickness Tolerance 厚度公差	$\pm 5 \mu\text{m}$	
Stack Thickness 板叠厚度	280-1150 μm	
Dopant Type 掺杂剂类型	N or P	
Doping 掺杂	N type: Phos, Red Phos, Sb & As P type: Boron	
Resistivity 电阻率	$\leq 0.001 - \geq 10000 \Omega\text{-cm}$	
Growth Method 生长方式	CZ, MCZ or FZ	
Crystal Orientation 晶体定向	$\langle 100 \rangle$, $\langle 111 \rangle$ or $\langle 110 \rangle$	
Backside Finish 背面处理	Lapped/Etched or Polished	
Buried Oxide Specifications 氧化物埋层规格		
Thermally Oxidised Buried Oxide Thickness 热氧化埋层厚度	0.2 – 4.0 μm grown on Handle, Device or both wafers 0.1 – 3.0 μm grown on Handle, Device or both wafers (<i>for Thin SOI</i>)	
Device Layer Specifications 顶层规格		
Device Layer Thickness 顶层厚度	$\geq 1.5 \mu\text{m}$	$\geq 5 \mu\text{m}$
	0.1 μm – 1 μm (<i>for Thin SOI</i>)	
Tolerance 公差	$\pm 0.5 \mu\text{m}$	$\pm 0.8 \mu\text{m}$
	$\pm 20\text{nm}$ (<i>for Thin SOI</i>)	
Dopant Type 掺杂剂类型	N or P	
Doping 掺杂	N type: Phos, Red Phos, Sb & As P type: Boron	
Resistivity 电阻率	$\leq 0.001 - \geq 10000 \Omega\text{-cm}$	
Growth Method 生长方式	CZ, MCZ or FZ	
Crystal Orientation 晶体定向	$\langle 100 \rangle$, $\langle 111 \rangle$ or $\langle 110 \rangle$	
Buried Layer Implant 埋层植入	N type or P type	

Applications 应用方向:

Advanced pressure sensors 压力传感器
 Accelerometers 加速度计
 Gyroscopes 陀螺仪
 Microfluidics/flow sensors 微流体/流量传感器
 RF MEMS 射频微机电系统
 MOEMs/Optical MEMs 多项/光学微机电系统
 Optoelectronics 光电工程
 Smart Power 智能电源
 Advanced Analog ICs 先进模拟集成电路
 Microphones 麦克风
 Luxury watches 名贵腕表

End Markets 终端市场:

Telecommunications 电讯
 Medical 医疗
 Automotive 汽车
 Consumer 消费品
 Instrumentation 仪表仪器

上海礴钛光电技术发展有限公司

Shanghai BonTek Optoelectronic Technology

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